STARPOWER

SEMICONDUCTOR **IGBT**

GD200HFT120C2S_T4F

Molding Type Module

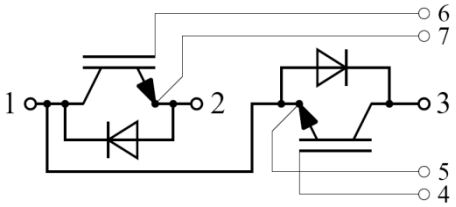
1200V/200A 2 in one-package

General Description

STARPOWER IGBT Power Module provides ultrafast switching speed as well as short circuit ruggedness.They are designed for the applications such as welding machine and inductive heating.

Features

- Low $V_{CE(sat)}$ Trench IGBT technology
- Low switching loss
- 10μs short circuit capability
- Low inductance case
- $V_{CE(sat)}$ with positive temperature coefficient
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper baseplate using DBC technology



Equivalent Circuit Schematic

Typical Applications

- Switching mode power supply
- Inductive heating
- Welding machine

Absolute Maximum Ratings T_C=25℃ unless otherwise noted

Symbol	Description	GD200HFT120C2S_T4F	Units
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	±20	V
I_C	Collector Current @ T_C=25℃ @ T_C=100℃	300 200	A
I_{CM}	Pulsed Collector Current t_p=1ms	400	A
I_F	Diode Continuous Forward Current	200	A
I_{FM}	Diode Maximum Forward Current t_p=1ms	400	A
P_D	Maximum Power Dissipation @ T_j=175℃	1119	W
T_{jmax}	Maximum Junction Temperature	175	℃
T_{jop}	Operating Junction Temperature	-40 to +150	℃
T_{STG}	Storage Temperature Range	-40 to +125	℃
V_{ISO}	Isolation Voltage RMS,f=50Hz,t=1min	4000	V
Mounting Torque	Power Terminal Screw:M6 Mounting Screw:M6	2.5 to 5.0 3.0 to 5.0	N.m
Weight	Weight of Module	300	g

Electrical Characteristics of IGBT T_C=25℃ unless otherwise noted

Off Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage	T_j=25℃	1200			V
I_{CES}	Collector Cut-Off Current	V_{CE}=V_{CES},V_{GE}=0V, T_j=25℃			5.0	mA
I_{GES}	Gate-Emitter Leakage Current	V_{GE}=V_{GES},V_{CE}=0V, T_j=25℃			400	nA

On Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	I_C=7.6mA,V_{CE}=V_{GE}, T_j=25℃	5.1	5.8	6.4	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	I_C=200A,V_{GE}=15V, T_j=25℃		2.05	2.45	V
		I_C=200A,V_{GE}=15V, T_j=125℃		2.40		

Switching Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$t_{d(on)}$	Turn-On Delay Time	V_{CC}=600V,I_C=200A, R_G=4.7Ω,V_{GE}=±15V, T_j=25℃		362		ns
t_r	Rise Time			112		ns
$t_{d(off)}$	Turn-Off Delay Time			378		ns
t_f	Fall Time			115		ns
E_{on}	Turn-On Switching Loss			17.4		mJ
E_{off}	Turn-Off Switching Loss			9.50		mJ
$t_{d(on)}$	Turn-On Delay Time	V_{CC}=600V,I_C=200A, R_G=4.7Ω,V_{GE}=±15V, T_j=125℃		364		ns
t_r	Rise Time			113		ns
$t_{d(off)}$	Turn-Off Delay Time			405		ns
t_f	Fall Time			125		ns
E_{on}	Turn-On Switching Loss			21.5		mJ
E_{off}	Turn-Off Switching Loss			15.4		mJ
C_{ies}	Input Capacitance	V_{CE}=25V,f=1MHz, V_{GE}=0V		12.3		nF
C_{res}	Reverse Transfer Capacitance			0.69		nF
I_{SC}	SC Data	t_P≤10μs,V_{GE}=15V, T_j=125℃,V_{CC}=900V, V_{CEM}≤1200V		800		A
R_{Gint}	Internal Gate Resistance			3.8		Ω
L_{CE}	Stray Inductance				20	nH
$R_{CC'+EE'}$	Module Lead Resistance, Terminal To Chip			0.35		mΩ

Electrical Characteristics of Diode T_C=25℃ unless otherwise noted

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Units
V_F	Diode Forward Voltage	I_F=200A	T_j=25℃		1.95	2.35	V
			T_j=125℃		2.05		
Q_r	Recovered Charge	I_F=200A, V_R=600V, R_G=4.7Ω, V_{GE}=-15V	T_j=25℃		10.1		μC
			T_j=125℃		21.5		
I_{RM}	Peak Reverse Recovery Current		T_j=25℃		113		A
			T_j=125℃		170		
E_{rec}	Reverse Recovery Energy		T_j=25℃		5.07		mJ
			T_j=125℃		13.6		

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case (per IGBT)		0.134	K/W
$R_{\theta JC}$	Junction-to-Case (per Diode)		0.194	K/W
$R_{\theta CS}$	Case-to-Sink (Conductive grease applied)	0.035		K/W

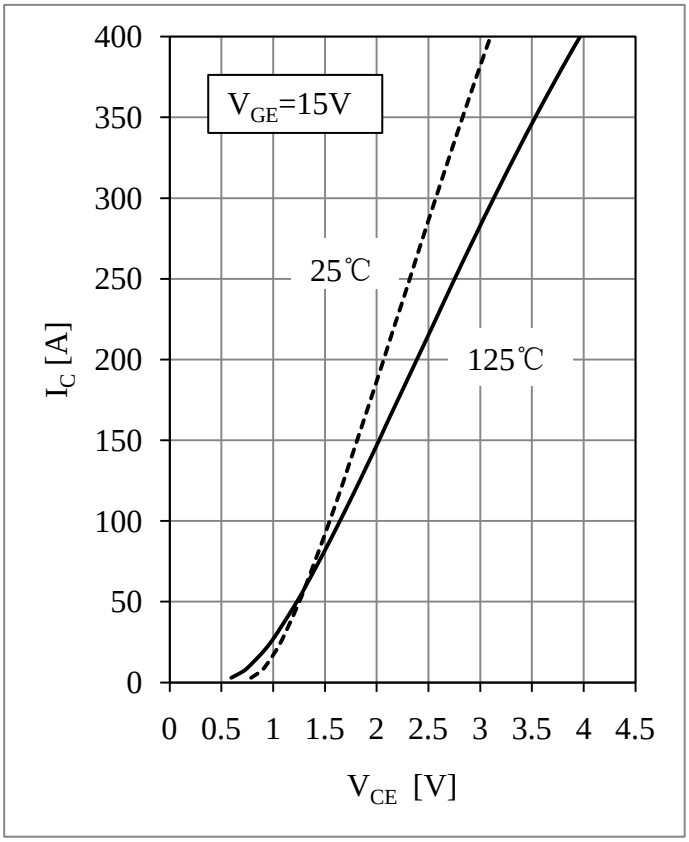


Fig 1. IGBT Output Characteristic

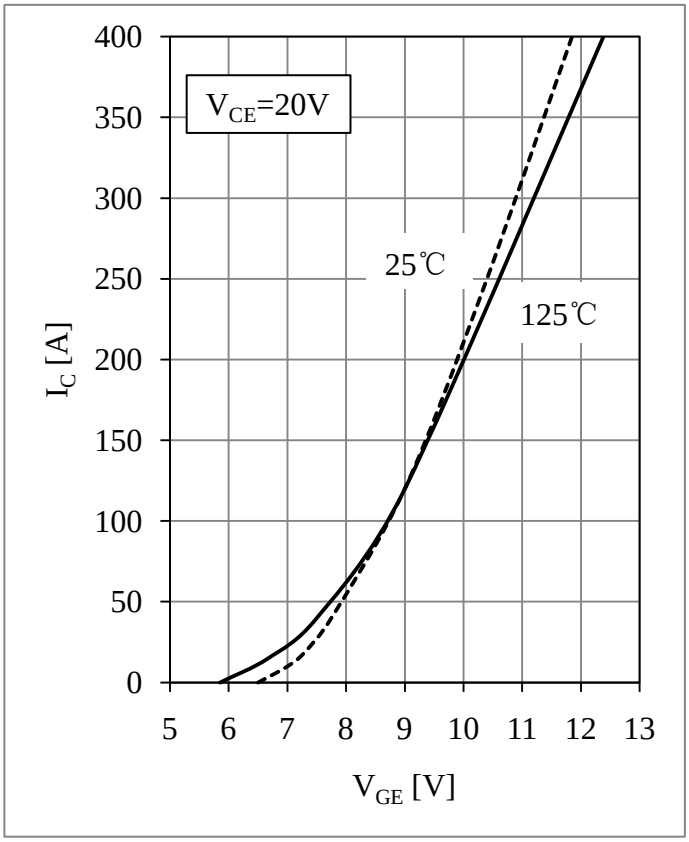


Fig 2. IGBT Transfer Characteristic

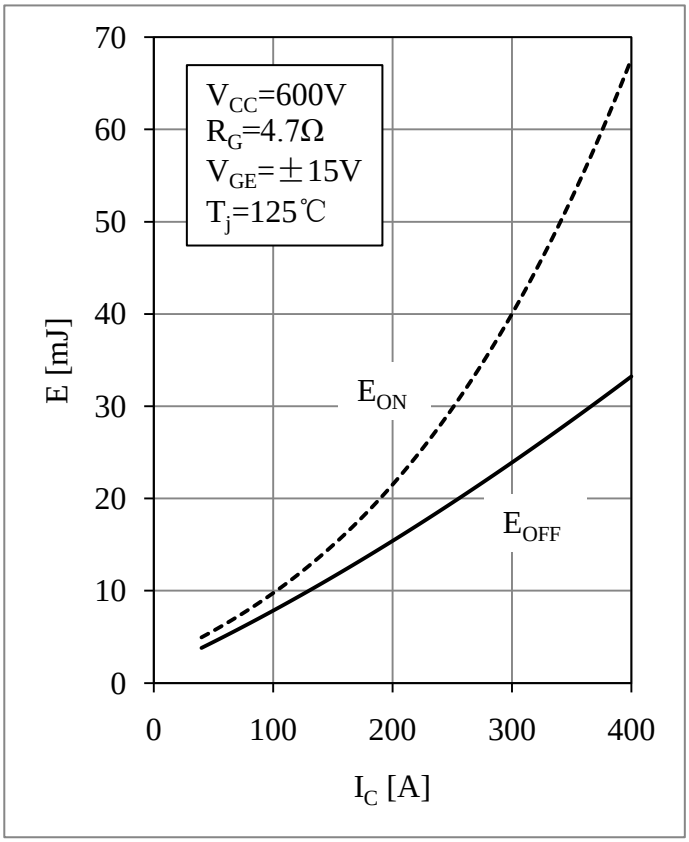


Fig 3. IGBT Switching Loss vs. I_C

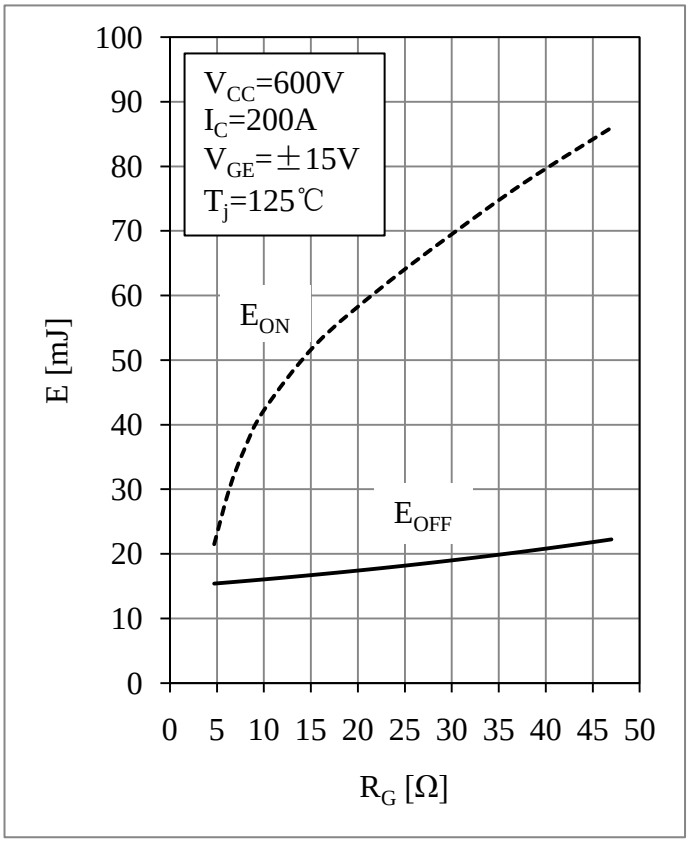


Fig 4. IGBT Switching Loss vs. R_G

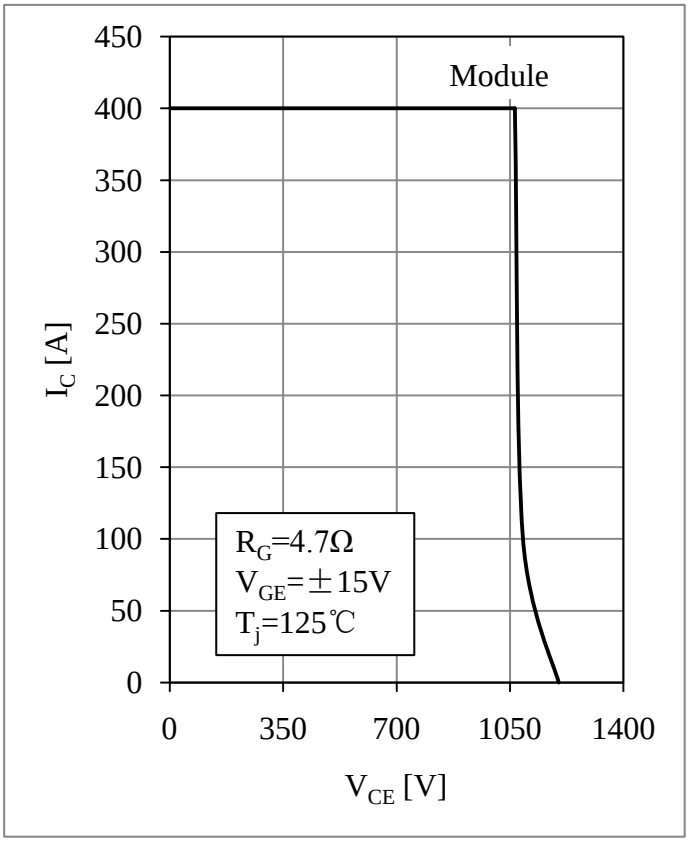


Fig 5. RBSOA

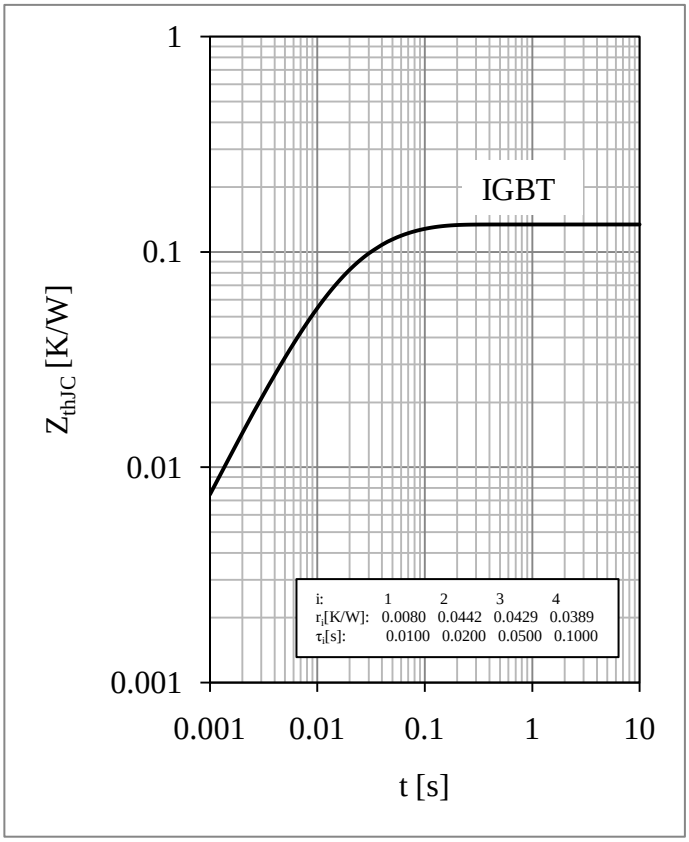


Fig 6. IGBT Transient Thermal Impedance

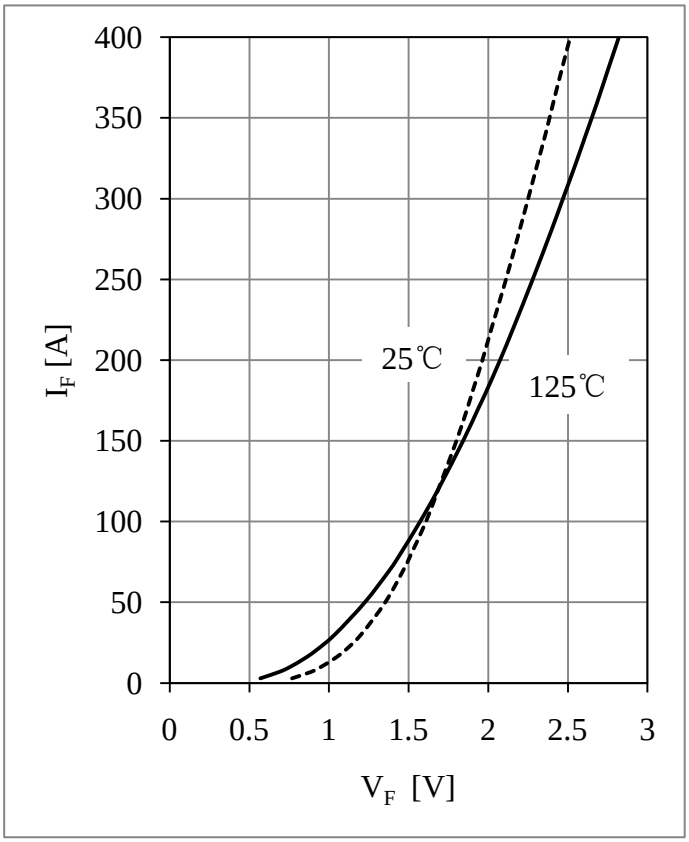


Fig 7. Diode Forward Characteristic

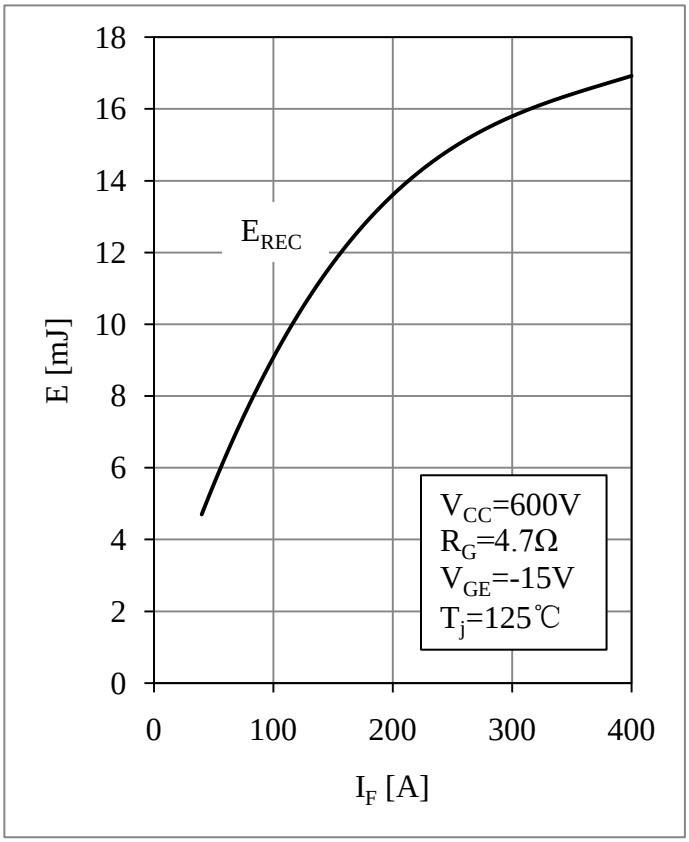


Fig 8. Diode Switching Loss vs. I_F

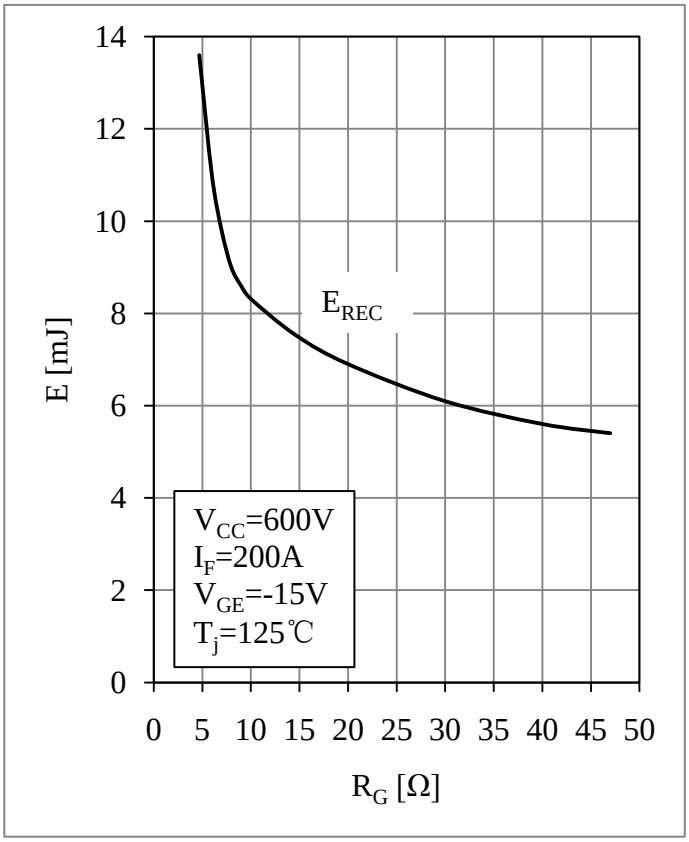


Fig 9. Diode Switching Loss vs. R_G

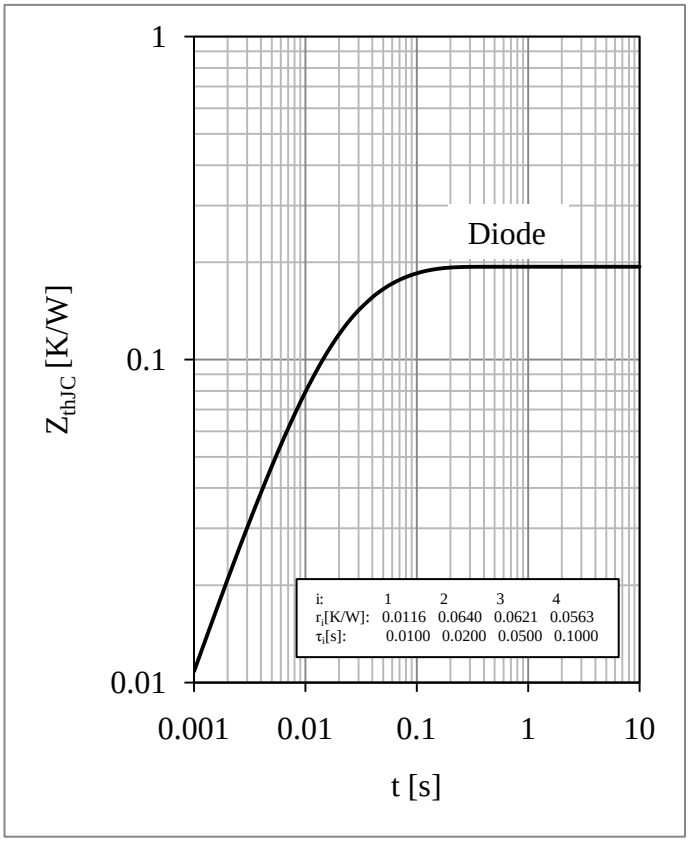
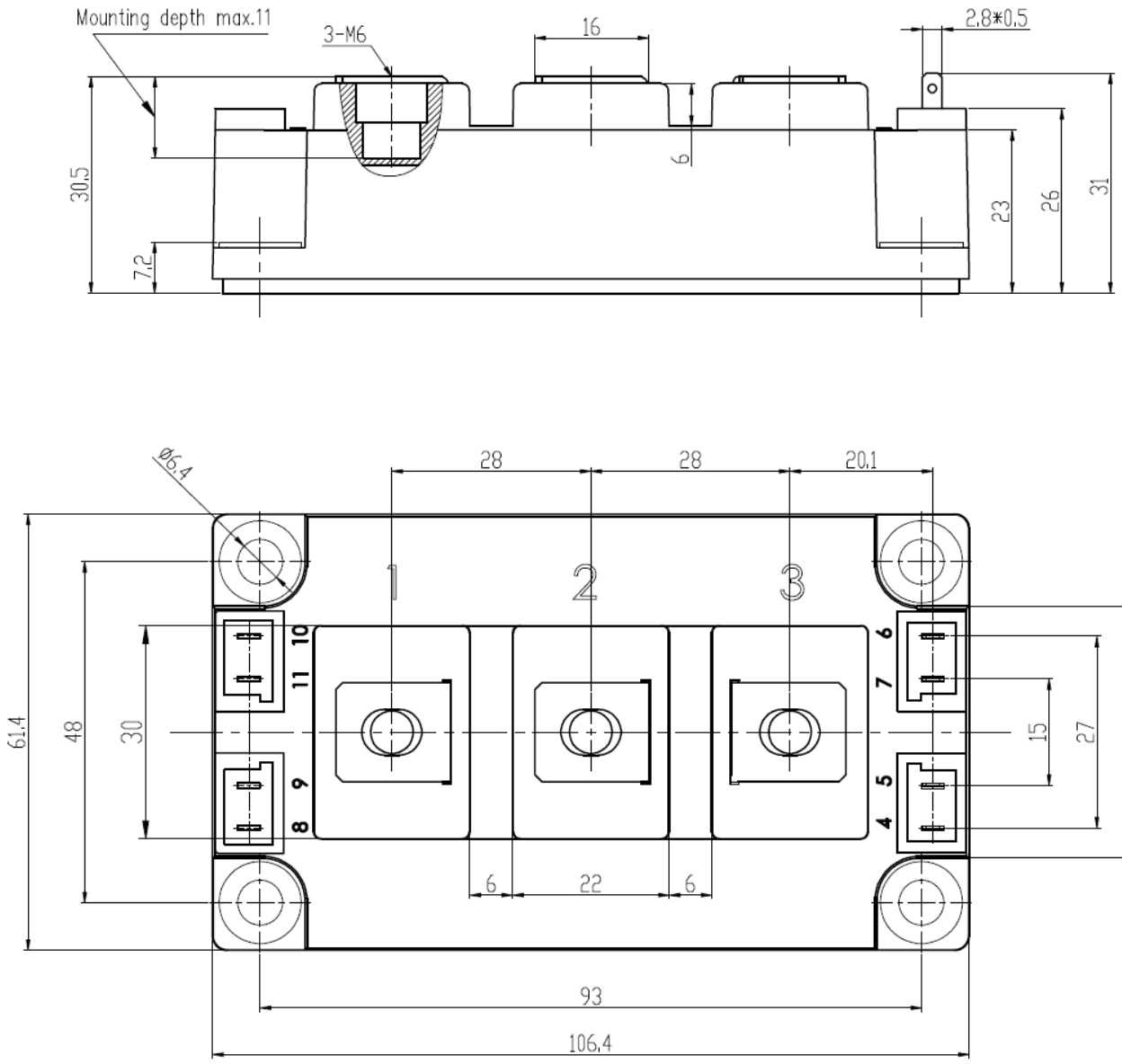


Fig 10. Diode Transient Thermal Impedance

Package Dimensions

Dimensions in Millimeters



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